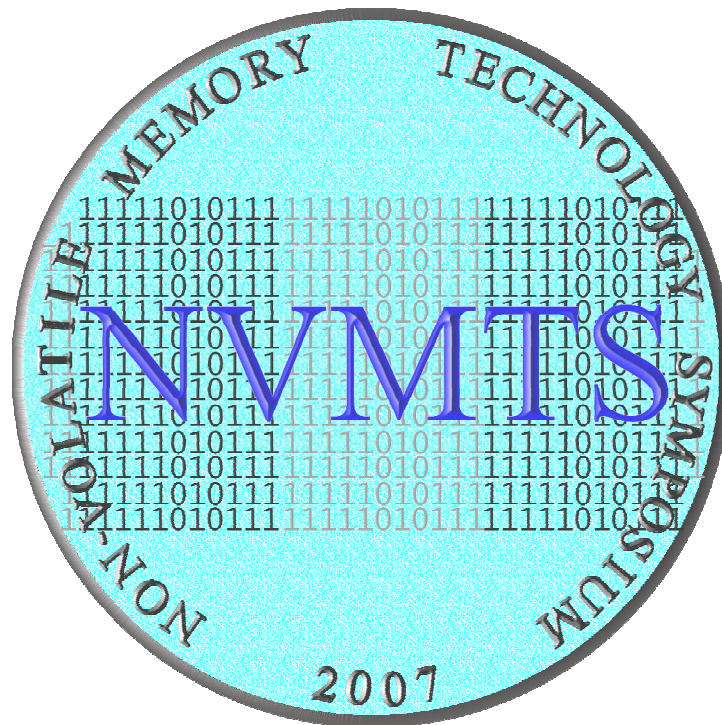




*Proceedings*

# 2007 Non-Volatile Memory Technology Symposium



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